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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/538,284	06/29/2005	Ho Seob Kim	KIMH3005/REF	2017
23364 BACON & TH	7590 07/03/2007 OMAS. PLLC		EXAMINER	
625 SLATERS FOURTH FLO	LANE		JOHNSTON	, PHILLIP A
	EXANDRIA, VA 22314		. ART UNIT	PAPER NUMBER
			2881 .	
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		,	MAIL DATE	DELIVERY MODE
			07/03/2007	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

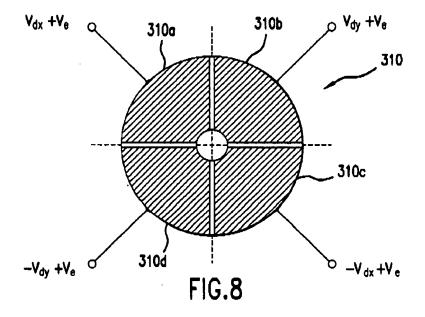
The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(a)			
		Applicant(s)			
Office Action Summary	10/538,284	KIM ET AL.			
Onice Action Summary	Examiner	Art Unit			
	Phillip A. Johnston	2881			
The MAILING DATE of this communication ap Period for Reply	opears on the cover sheet w	ith the correspondence address			
A SHORTENED STATUTORY PERIOD FOR REP WHICHEVER IS LONGER, FROM THE MAILING I Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory perior Failure to reply within the set or extended period for reply will, by statu Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNION (1) 136(a). In no event, however, may a red will apply and will expire SIX (6) MONUTE, cause the application to become AE	CATION. reply be timely filed VTHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).			
Status		•			
1) Responsive to communication(s) filed on 29.	June 2005				
_					
3) Since this application is in condition for allow		ters, prosecution as to the merits is			
closed in accordance with the practice under					
Disposition of Claims					
4)⊠ Claim(s) <u>1-13</u> is/are pending in the applicatio	· ·				
4a) Of the above claim(s) is/are withdra					
5) Claim(s) is/are allowed.					
6)⊠ Claim(s) <u>1-13</u> is/are rejected		· ·			
7) Claim(s) is/are objected to					
8) Claim(s) are subject to restriction and/	or election requirement.				
Application Papers					
9)☐ The specification is objected to by the Examir	nor.				
10)⊠ The drawing(s) filed on 29 June 2005 is/are:		cted to by the Examiner			
Applicant may not request that any objection to the		-			
Replacement drawing sheet(s) including the corre					
11) The oath or declaration is objected to by the E					
Priority under 35 U.S.C. § 119					
12)⊠ Acknowledgment is made of a claim for foreig	In priority under 35 U.S.C. 8	\$ 119(a)-(d) or (f)			
a)⊠ All b)□ Some * c)□ None of:	, , , , , , , , , , , , , , , , , , , ,	, , , , , , , , , , , , , , , , , , , ,			
1 Certified copies of the priority documer	nts have been received.				
2 Certified copies of the priority documer		pplication No			
3. Copies of the certified copies of the pri-					
application from the International Burea					
* See the attached detailed Office action for a lis	st of the certified copies not	received.			
Attachment(s)					
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)		Summary (PTO-413) s)/Mail Date			
Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date 6-29-2005.	5) Notice of Ir	nformal Patent Application			
1 aper 140(5)/191811 Date 0-29-2003.	6)	 ·			

Detailed Action

Claims Rejection - 35 U.S.C. 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
- (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which the subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-13 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Patent No. 6,288,401 to Chang, in view of Winkler, U.S. Patent No. 6,943,507.
- 3. Regarding claim 1, Chang teaches centering extraction electrode 310 (note Figure 8 below) fabricated on a silicon substrate that includes four electrode elements 310a, 310b, 310c, and 310d (a plurality of sensing regions), which are separated by (divided by) insulating layers. Col. 5, line 6-18; and line 62-67.

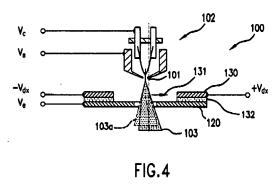


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Chang also teaches that voltages ranging from a few tens of volts to a few hundred volts are applied to the extraction electrodes centering regions to correct for beam misalignment (note Figure 4 below). Col. 4, line 22-54.

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It is implied in Chang above that, in order to define the voltage range applied to the extraction electrodes centering regions to keep the beam centered, one would have detected the beam striking the centering regions, or encountered misaligned emitters that produced off axis beams that struck the centering regions. However Chang fails to teach the electron beam striking the centering (sensing) regions.

4. Winkler teaches an electron beam micro-column 2-1 (Note Figure 2a below) where an extractor electrode 2-4 is connected via conducting lines to current sensing unit 2-24 that measures the amount of beam current absorbed (striking) by the extraction electrode. See Col. 10, line 62-67; and Col. 11, line 1-7.

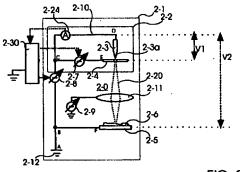


FIG. 2a

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5. Winkler modifies Chang to provide sensing of the amount of beam current absorbed (striking) in the extractor electrode.

- 6. Therefore it would have been obvious to one of ordinary skill in the art that Chang would use the divided extraction electrode to sense a beam current striking the centering regions and deflect the beam back to ensure that the electron beam is aligned with the optical axis.
- 7. Regarding claims 2 and 3, Chang teaches that the centering electrode regions have a conductive layer, such as aluminum, gold, silicon (that is heavily n doped) or other conductive material deposited over the insulating layer. Col. 4, line 1-11.

It is also implied herein that, Chang's use of n-doped silicon technology to fabricate the centering (sensing) regions, would also include the use of p-n junctions.

8. Regarding claims 4 and 5, the rational applied above regarding claim 1, also applies to the structural limitations of claims 4 and 5, wherein Chang's teaching of centering the beam would include determining (verifying and calculating) which centering (sensing) region requires the proper bias amount to deflect the misaligned beam back on axis. Chang also teaches that prealignment of the emitter is mechanically performed, and when the electron emitter is properly prealigned with optical axis no centering potential is necessary, and uniform bias potential Vb is applied to all individual electrode elements so that a uniform extraction field is preserved. Col. 1, line 65-67; and Col. 4, line 34-40.

It is important to point out here that Chang teaches correcting misalignment between the electron emitter and the optical axis using both mechanical prealignment

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and electrostatic beam centering, where electrostatic beam centering aligns the electron beam to the optical axis with the same or greater precision as with the conventional mechanical alignment.

In other words, Chang does not teach away from the claimed invention, but merely provides an optional or alternative means for centering the beam after conventional mechanical alignment of the emitter with the extractor, and only obviating the necessity of an extremely precise mechanical alignment, which is consistent with the applicants stated need for a method to easily and precisely align the electron emitter with the extractor hole.

- 9. Regarding claim 6, the rational applied above to claim 1, also applies to claim 6. In addition it is recognized herein that the limitation regarding; "sensing regions through which the electrons of the electron beam can be electrically transmitted" refers to the electrically conductive regions recited in claim 1.
- 10. Regarding claims 7 and 8, the rational applied above to claims 2 and 3, also applies to claims 7 and 8, wherein Winkler and Chang teach sensing regions that include conductive materials, and p-n junctions.
- 11. Regarding claim 9, the rational applied above regarding claim 1, also applies to the structural limitations of claim 9, wherein Winkler and Chang teach providing electron emitter at a first side of an object to be measured; providing an electron beam measuring device at a second side of the object to be measured, said electron beam measuring device including a plurality of sensing regions through which the electrons of the electron beam can be electrically transmitted, and insulating portions including

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insulating material for prevention of the electron flow or low-doped semiconductor for reduction of the electron flow and dividing each of the sensing regions; sensing the electrons emitted from said electron emitter in each of the sensing regions; verifying position of the sensing regions being in a state of sensing the electrons in said electron beam measuring device and calculating the amount of the electrons striking each of the sensing regions; and calculating relative position of the first and the second sides on the basis of the measured data related to the position of each of the sensing regions being in a state of sensing the electrons and the striking amount of the electrons.

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12. Regarding claim 10, the rational applied above regarding claims 1, 4 and 5, also applies to the structural limitations of claim 10, wherein Winkler and Chang teach, providing electron emitter at a first side of an object to be aligned; providing an electron beam measuring device at a second side of the object to be aligned, said electron beam measuring device including a plurality of sensing regions through which the electrons of the electron beam can be electrically transmitted, and insulating portions including insulating material for prevention of the electron flow or low-doped semiconductor for reduction of the electron flow and dividing each of the sensing regions; sensing the electrons emitted from said electron emitter in each of the sensing regions; verifying position of the sensing regions being in a state of sensing the electrons in said electron beam measuring device and calculating the amount of the electrons striking each of the sensing regions; calculating relative position of the first and the second sides on the basis of the measured data related to the position of each

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of the sensing regions being in a sensing state and the striking amount of the electrons; and moving either one of the first or second side, or both the first and second sides on the basis of the verified relative position.

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- 13. Regarding claim 11, the rational applied above regarding claim 10, also applies to the structural limitations of claim 11, wherein Chang also teaches deflecting the electron beam to be approximately parallel with the optical axis, e.g., within 3 milliradians, which implies calculating a beam parallelism (alignment) value in accordance with Chang. Col. 5, line 44-54.
- 14. Regarding claims 12 and 13, the rational applied above regarding claims 1,4, and 5, also applies to the structural limitations of claims 12 and 13, wherein Winkler and Chang teach verifying the position of the sensing region being in a state of currently sensing electrons and the amount of the current flow; calculating relative position between the extractor aperture and the electron emitter on the basis of the verified sensing region and the amount of the current flow; and moving said electron emitter, said extractor, or said electron emitter and said extractor according to said calculated data.

Conclusion

15. Any inquiry concerning this communication or earlier communications should be directed to Phillip Johnston whose telephone number is (571) 272-2475. The examiner can normally be reached on Monday-Friday from 7:30 am to 4:00 pm. If attempts to reach the examiner by telephone are unsuccessful, the examiners supervisor Robert Kim

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can be reached at (571)272-2293. The fax phone number for the organization where the application or proceeding is assigned is 571 273 8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

PJ

June 19, 2007

RUBERT KIM SUPERVISORY PATENT EXAMINER